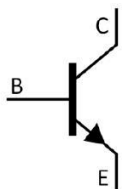


Silicon NPN transistor in a TO-18 Plastic Package.

High V_{CEO} , Large DC current, high f_T , low $V_{CE(sat)}$.

Low power audio amplifier, high speed switching applications.



PIN1 Emitter PIN 2 Collector PIN 3 Base

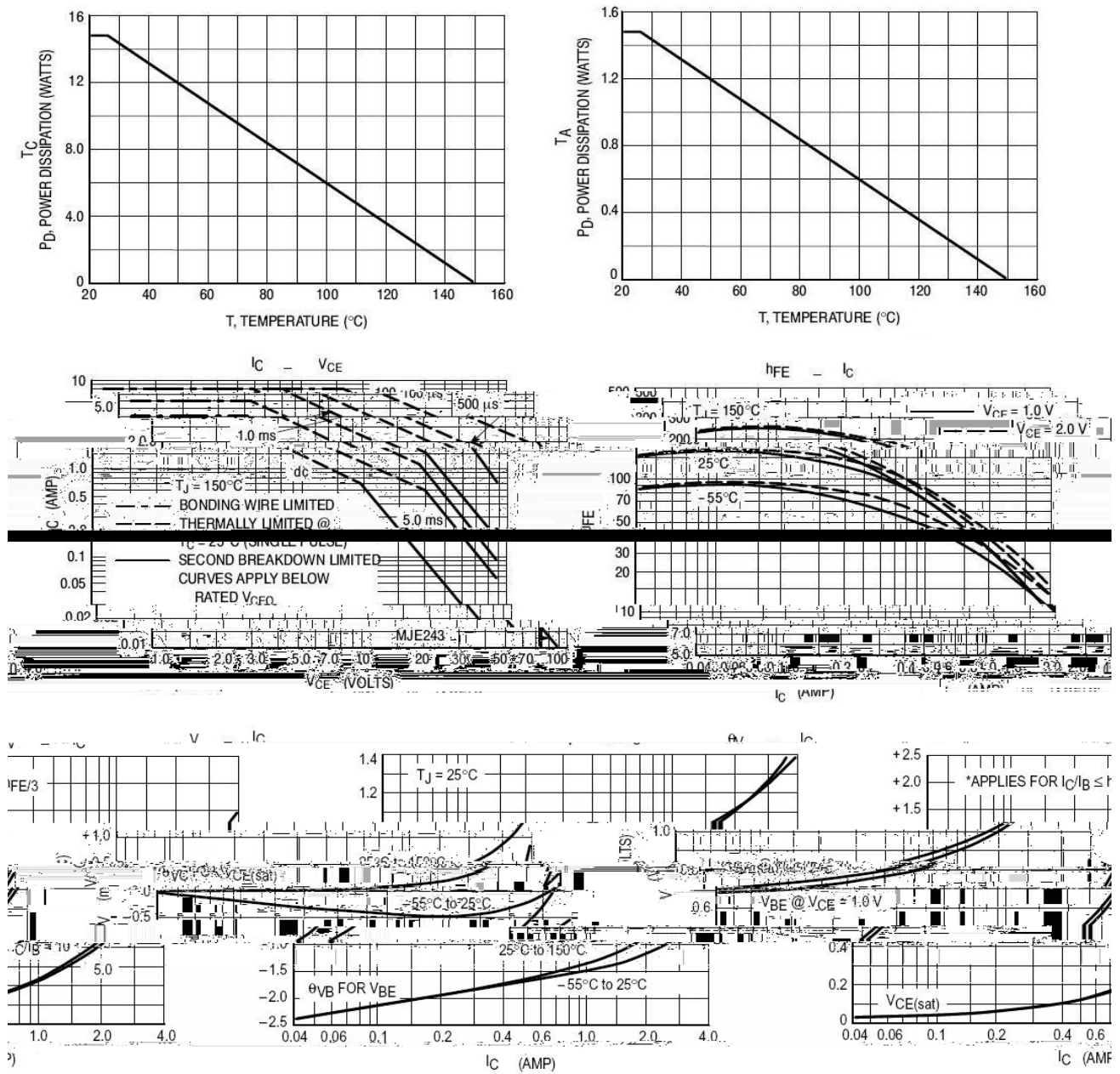
/ h_{FE} Classifications & Marking

See Marking Instructions.

t71 Tf 0 -4.2057 TD <090004390bba0bc843 018< .5 01 -0

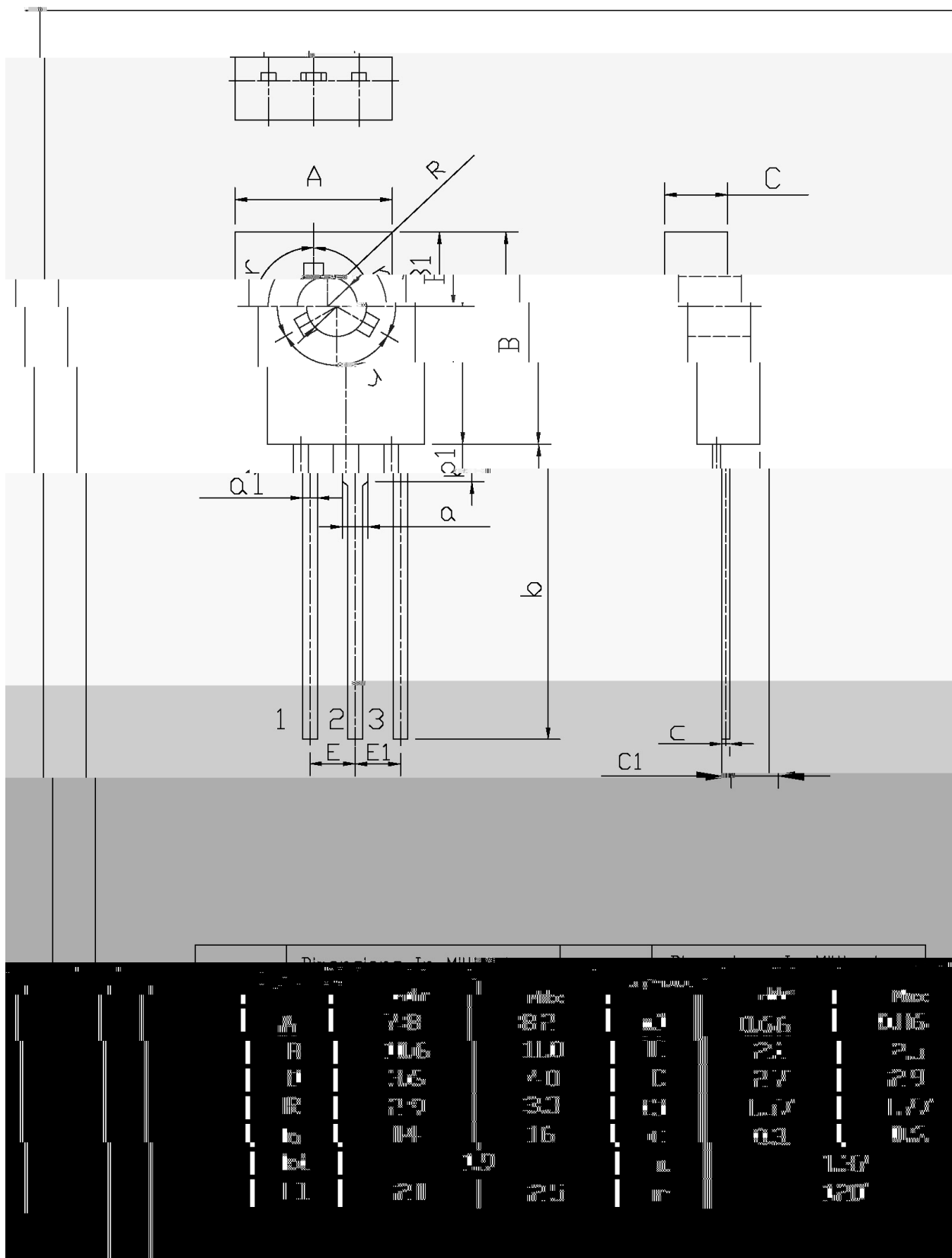
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	100	V
Collector to Emitter Voltage	V_{CEO}	100	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Collector Current - Continuous	$I_{C(1)}$	4.0	A
	$I_{C(2)}$	8.0	A
Peak Collector Current	I_B	10	A
Collector Power Dissipation	P_D	1.5	W
Collector Power Dissipation	$P_D(T_c=25^\circ C)$	15	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55~150	

/ Electrical Characteristic Curve

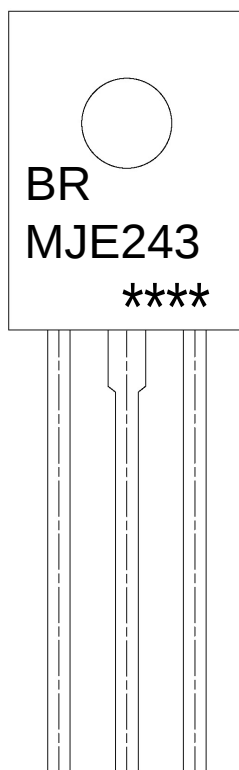


T0-126

单位: 



/ Marking Instructions



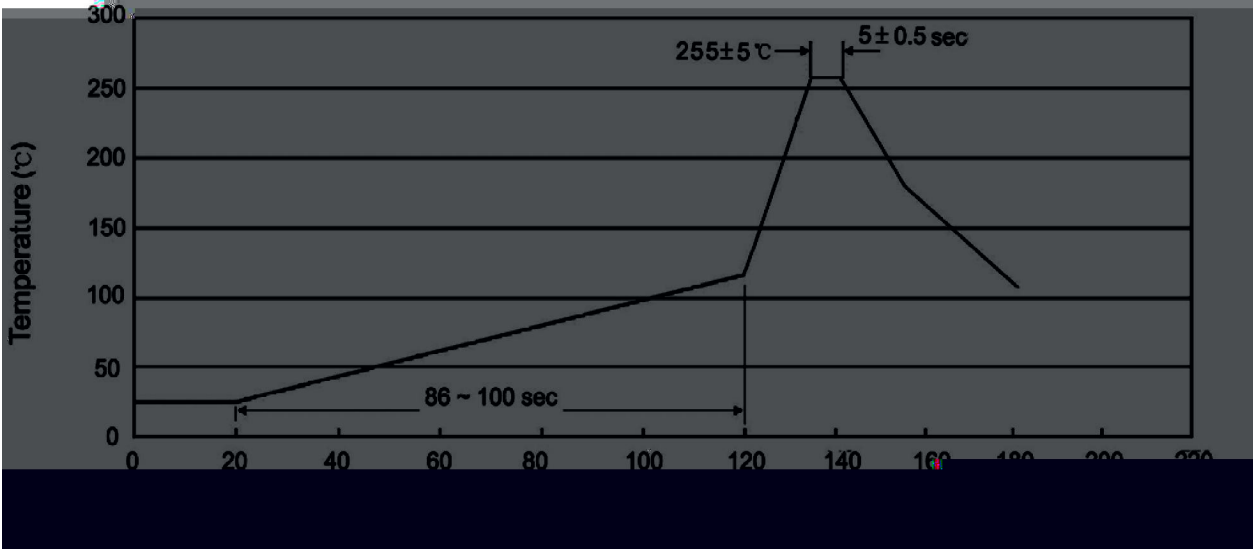
Note:

BR: Company Code

MJE243: Product Type.

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- 1

25 150

60 90sec;
- 2

255 5

5 0.5sec;
- 3

2 10

/sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:255 5

, Duration:5 0.5sec.
3. Cooling Speed: 2~10

/sec.

/ Resistance to Soldering Heat Test Conditions

270 5 10 1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱